

Title (en)

SOLDERING FILLER METAL, ASSEMBLY METHOD FOR SEMICONDUCTOR DEVICE USING SAME, AND SEMICONDUCTOR DEVICE

Title (de)

WEICHLÖTZZUSATZMETALL, ZUSAMMENBAU EINER HALBLEITERANORDNUNG MIT VERWENDUNG DIESES LOT UND HALBLEITERANORDNUNG

Title (fr)

MÉTAL D'APPORT DE SOUDAGE, PROCÉDE D'ASSEMBLAGE POUR DISPOSITIF A SEMI-CONDUCTEUR AU MOYEN DU MÉTAL, ET DISPOSITIF A SEMI-CONDUCTEUR

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Application

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Abstract (en)

[origin: WO2004026527A1] In conventional Sn/Sb type brazing filler metals, there are disadvantages that large grains in a beta ' phase are likely to deposit and that cracks are likely to occur in the elements and the bonded portion, and that voids are formed when the above described special coating is provided on the die bonding plane of the semiconductor element. The brazing filler metal of the present invention comprises 5 to 20 weight % of Sb and 0.01 to 5 weight % of Te, with the balance being Sn and incidental impurities, or a brazing filler metal comprises 5 to 20 weight % of Sb, 0.01 to 5 weight % of Te, 0.001 to 0.5 weight % of P, with the balance being Sn and incidental impurities.

IPC 8 full level

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